

ABSTRACT

There is provided a technique that includes: (a) lowering a temperature in a process chamber supplied with a cleaning gas containing a halogen element while being heated to a first temperature, from the first temperature to a second temperature equal to or lower than a temperature at which substrate processing is performed in the process chamber, while vacuum-exhausting an inside of the process chamber; and (b) after (a), supplying a gas containing a water vapor into the process chamber while vacuum-exhausting the inside of the process chamber, to cause the halogen element remaining in the process chamber to react with the water vapor.

FIG. 5